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QUERY CONTROL FORM				RTIS USE ONLY	
Application No.	09/782,446	Prepared by	MPB	Tracking Number	0509/1147
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JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION

a. Page Missing
b. Text Continuity
c. Holes through Data
d. Other Missing Text
e. Illegible Text
f. Duplicate Text
g. Brief Description
h. Sequence Listing
i. Appendix
j. Amendments
k. Other

CLAIMS

a. Claim(s) Missing
b. Improper Dependency
c. Duplicate Numbers
d. Incorrect Numbering
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f. Punctuation
g. Amendments
h. Bracketing
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MESSAGE

Claim 3 (originally claim 25) depends on a cancelled claim 1 - original claim 1.

Please advise/correct claim dependency.

Thanh Nguyen

initials

RESPONSE

initials

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber with a flow rate from about 300 sccm to about 800 sccm;

generating a plasma from the NH3, which etches the organic dielectric layer; and

maintaining the substrate at a temperature between about 10° C to about 40° C during the etching of the organic dielectric layer.

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25. (Previously Presented) The method, as recited in claim 1, further comprising providing a bias power of between about 0 W and 100 W during etching of the organic dielectric layer.

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26. (Previously Presented) The method, as recited in claim 13, further comprising providing a bias power of between about 0 W and 100 W during etching of the organic low-k dielectric layer.

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27. (Previously Presented) The method, as recited in claim 13, further comprising:

placing an etch stop layer over the organic low-k dielectric layer;

placing a second organic low-k dielectric layer over the etch stop layer, wherein the second organic low-k dielectric layer is between the organic low-k dielectric layer and the hardmask.

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28. (Previously Presented) The method, as recited in claim 27, further comprising etching the second organic low-k dielectric layer with a first etch, wherein the first etch provides a bias power of between about 250 W to about 2500 W before selectively etching the organic low-k dielectric layer.